

# FDS6299S

## 30V N-Channel PowerTrench® SyncFET™

### General Description

The FDS6299S is designed to replace a single SO-8 MOSFET and Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low  $R_{DS(ON)}$  and low gate charge. The FDS6299S includes a patented combination of a MOSFET monolithically integrated with a Schottky diode.

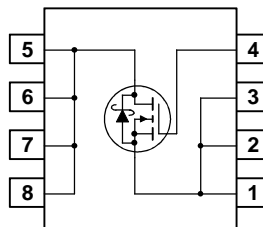
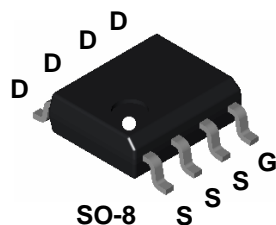
### Applications

- Synchronous Rectifier for DC/DC Converters
  - Notebook Vcore low side switch
  - Point of load low side switch



### Features

- 21 A, 30 V.  $R_{DS(ON)} = 3.9\text{ m}\Omega @ V_{GS} = 10\text{ V}$   
 $R_{DS(ON)} = 5.1\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- Includes SyncFET Schottky body diode
- High performance trench technology for extremely low  $R_{DS(ON)}$  and fast switching
- High power and current handling capability
- 100%  $R_G$  (Gate Resistance) tested
- Termination is Lead-free and RoHS Compliant



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Drain Current – Continuous (Note 1a)	21	A
	– Pulsed	105	
$P_D$	Power Dissipation for Single Operation (Note 1a)	2.5	W
	(Note 1b)	1.2	
	(Note 1c)	1	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	$-55$ to $+150$	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6299S	FDS6299S	13"	12mm	2500 units

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$ , Referenced to $25^\circ\text{C}$		22		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			500	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	1	1.7	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 10\text{ mA}$ , Referenced to $25^\circ\text{C}$		-5		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 21\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 19\text{ A}$ $V_{GS} = 10\text{ V}, I_D = 21\text{ A}, T_J = 125^\circ\text{C}$		3.3 4.1 4.5	3.9 5.1 5.6	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 21\text{ A}$		94		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		3880		pF
$C_{oss}$	Output Capacitance			1030		pF
$C_{riss}$	Reverse Transfer Capacitance			310		pF
$R_G$	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$	0.4	1.8	3.1	$\Omega$

**Switching Characteristics (Note 2)**

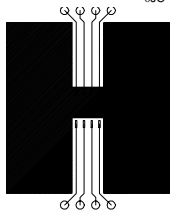
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		12	22	ns
$t_r$	Turn-On Rise Time			12	22	ns
$t_{d(off)}$	Turn-Off Delay Time			60	96	ns
$t_f$	Turn-Off Fall Time			35	56	ns
$Q_{g(TOT)}$	Total Gate Charge at $V_{GS}=10\text{V}$	$V_{DS} = 15\text{ V}, I_D = 21\text{ A}$		58	81	nC
$Q_g$	Total Gate Charge at $V_{GS}=5\text{V}$			31	43	nC
$Q_{gs}$	Gate-Source Charge			11		nC
$Q_{gd}$	Gate-Drain Charge			8		nC

**Drain-Source Diode Characteristics and Maximum Ratings**

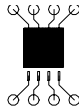
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 3.5\text{ A}$ (Note 2)		420	700	mV
$t_{rr}$	Diode Reverse Recovery Time	$I_F = 21\text{ A},$ $di_F/dt = 300\text{ A}/\mu\text{s}$ (Note 3)		32		ns
$I_{RM}$	Diode Reverse Recovery Current			2.1		A
$Q_{rr}$	Diode Reverse Recovery Charge			34		nC

**Notes:**

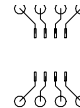
1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a) 50°/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b) 105°/W when mounted on a .04 in<sup>2</sup> pad of 2 oz copper



c) 125°/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2.0%.

3. See "SyncFET Schottky body diode characteristics" below.

### Typical Characteristics

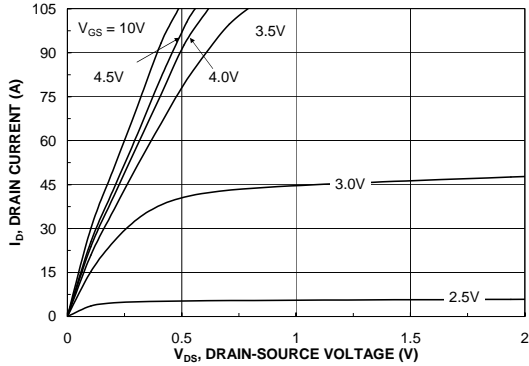


Figure 1. On-Region Characteristics.

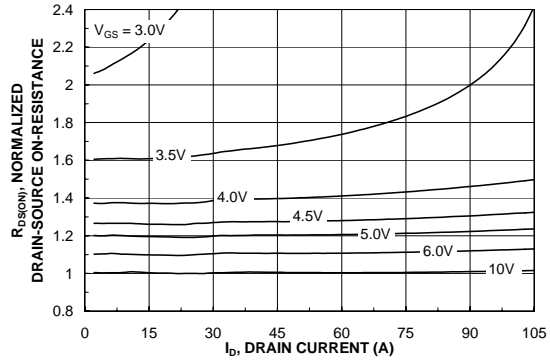


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

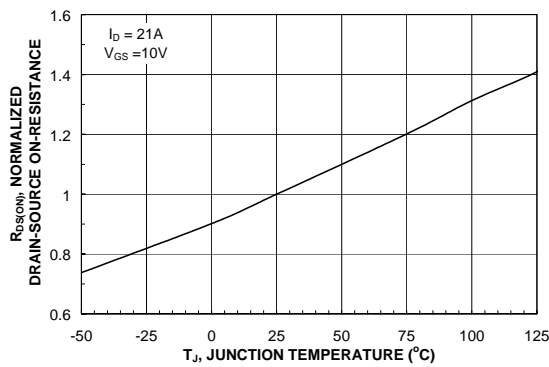


Figure 3. On-Resistance Variation with Temperature.

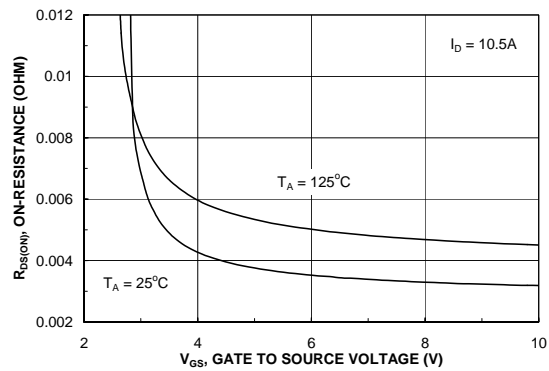


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

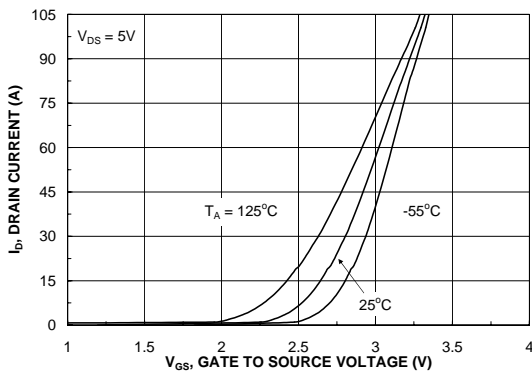


Figure 5. Transfer Characteristics.

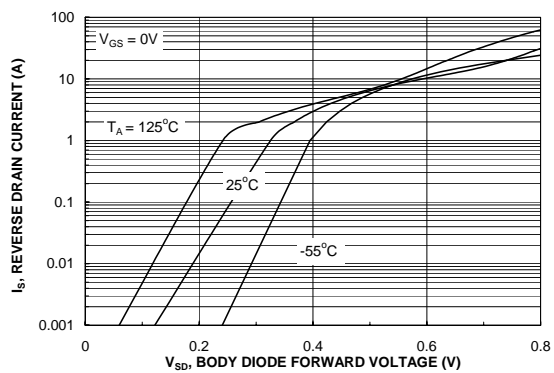
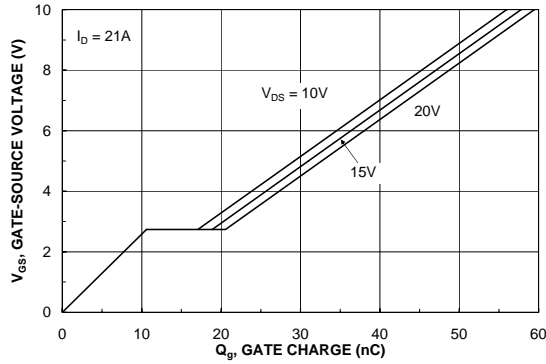
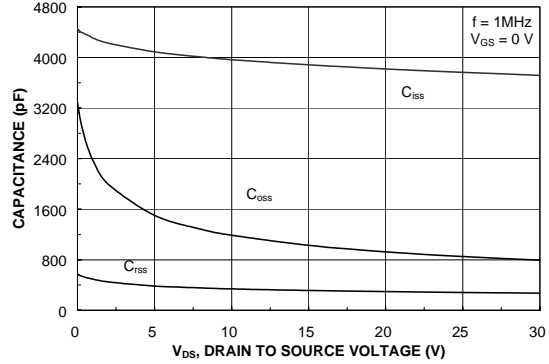


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

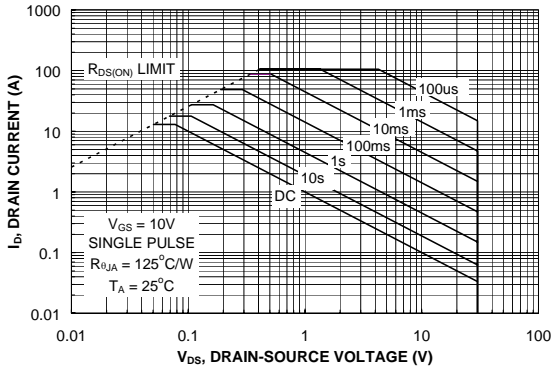
**Typical Characteristics** (continued)



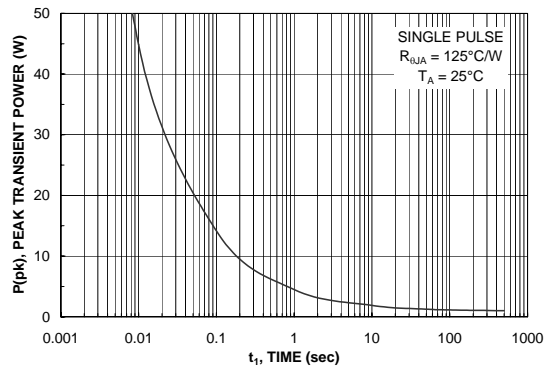
**Figure 7. Gate Charge Characteristics.**



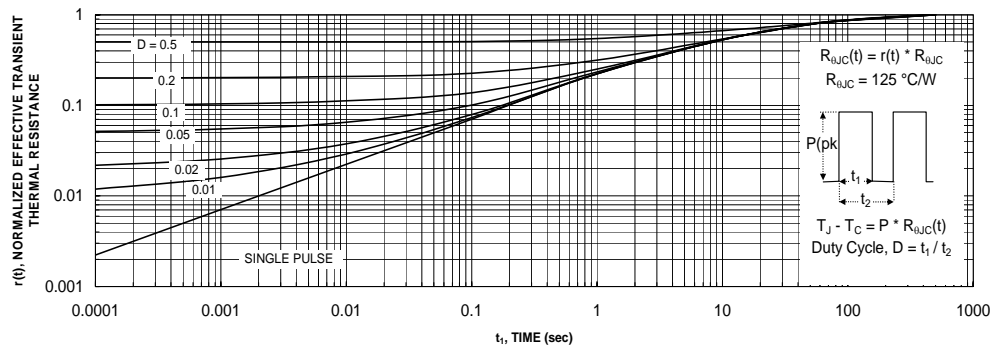
**Figure 8. Capacitance Characteristics.**



**Figure 9. Maximum Safe Operating Area.**



**Figure 10. Single Pulse Maximum Power Dissipation.**



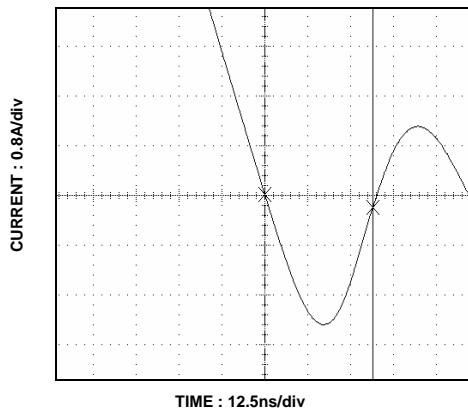
**Figure 11. Transient Thermal Response Curve.**

Thermal characterization performed using the conditions described in Note 1c.  
Transient thermal response will change depending on the circuit board design.

## Typical Characteristics (continued)

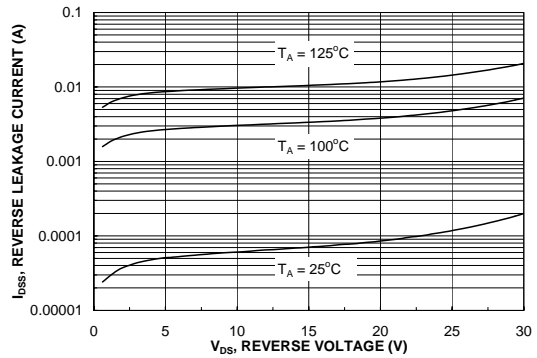
### SyncFET Schottky Body Diode Characteristics

Fairchild's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 shows the reverse recovery characteristic of the FDS6299S.



**Figure 12. FDS6299S SyncFET body diode reverse recovery characteristic.**

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.




**Figure 13. SyncFET body diode reverse leakage versus drain-source voltage and temperature.**



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